

ABSTRACT

The present invention is a polishing pad used for polishing a semiconductor substrate, wherein, at least, grooves having a radial pattern are formed on a surface of the polishing pad, and (an average value of the sum totals of the groove volumes in parts immediately below the substrate / area of the substrate) is 0.06 to 0.23, or the grooves are formed so that a groove depth of the groove parts located nearer to the center than the substrate is shallower than a groove depth of the groove parts existing immediately below the substrate, and an intersection point where the grooves overlap each other at the central part of the radial pattern of the grooves does not exist immediately below the substrate, a method for processing it, and a method for producing a substrate using this. Thereby, there can be provided a polishing pad, by which in the polishing of a semiconductor substrate, a required amount of a polishing agent is supplied to the central part of the substrate and thereby polishing can be performed with high flatness and furthermore the semiconductor substrate surface is not flawed because peeling, twist, or burr does not occur, a method for processing it, and a method for producing a substrate.